Switching Diode, Dual, High Voltage, Common Cathode

BAV23CL, NSVBAV23CL

Features

- Moisture Sensitivity Level: 1
- ESD Rating – Human Body Model: Class 2
  – Machine Model: Class C
- Fast Switching Speed
- Switching Application
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD TV
- Power Supply
- Industrial

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	250	V
Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Peak Forward Current	I_F	400	mA
Non−Repetitive Peak Forward Surge Current @ t = 1.0 μs @ t = 100 μs @ t = 10 ms	I_{FSM}	9.0 3.0 1.7	A
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc
Non−Repetitive Peak Per Human Body Model Per Machine Model	 HBM MM	 4.0 400	 kV V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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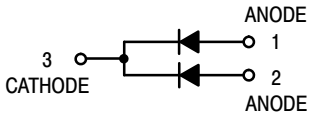
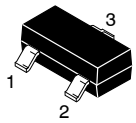
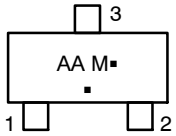




SOT−23
CASE 318
STYLE 9

MARKING DIAGRAM



AA = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BAV23CLT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BAV23CLT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel
NSVBAV23CLT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
SINGLE HEATED			
Total Device Dissipation (Note 1) T_A = 25°C Derate above 25°C	P_D	265 2.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	472	°C/W
Thermal Reference, Junction−to−Anode Lead (Note 1)	$R_{\_\psi JL}$	263	°C/W
Thermal Reference, Junction−to−Case (Note 1)	$R_{\_\psi JC}$	289	°C/W
Total Device Dissipation (Note 2) T_A = 25°C Derate above 25°C	P_D	345 2.7	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	362	°C/W
Thermal Reference, Junction−to−Anode Lead (Note 2)	$R_{\_\psi JL}$	251	°C/W
Thermal Reference, Junction−to−Case (Note 2)	$R_{\_\psi JC}$	250	°C/W
DUAL HEATED (Note 3)			
Total Device Dissipation (Note 1) T_A = 25°C Derate above 25°C	P_D	390 3.1	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	321	°C/W
Thermal Reference, Junction−to−Anode Lead (Note 1)	$R_{\_\psi JL}$	159	°C/W
Thermal Reference, Junction−to−Case (Note 1)	$R_{\_\psi JC}$	138	°C/W
Total Device Dissipation (Note 2) T_A = 25°C Derate above 25°C	P_D	540 4.3	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	231	°C/W
Thermal Reference, Junction−to−Anode Lead (Note 2)	$R_{\_\psi JL}$	148	°C/W
Thermal Reference, Junction−to−Case (Note 2)	$R_{\_\psi JC}$	119	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. FR-4 @ 100 mm^2, 1 oz. copper traces, still air.
2. FR-4 @ 500 mm^2, 2 oz. copper traces, still air.
3. Dual heated values assume total power is sum of two equally powered channels

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current (V_R = 200 Vdc) (V_R = 200 Vdc, T_J = 150°C)	I_R	 − −	 0.1 100	μAdc
Reverse Breakdown Voltage (I_{BR} = 100 μAdc)	$V_{(BR)}$	250	−	Vdc
Forward Voltage (I_F = 100 mAdc) (I_F = 200 mAdc)	V_F	 − −	 1000 1250	mV
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_T	−	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, R_L = 100 Ω)	t_{rr}	−	150	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

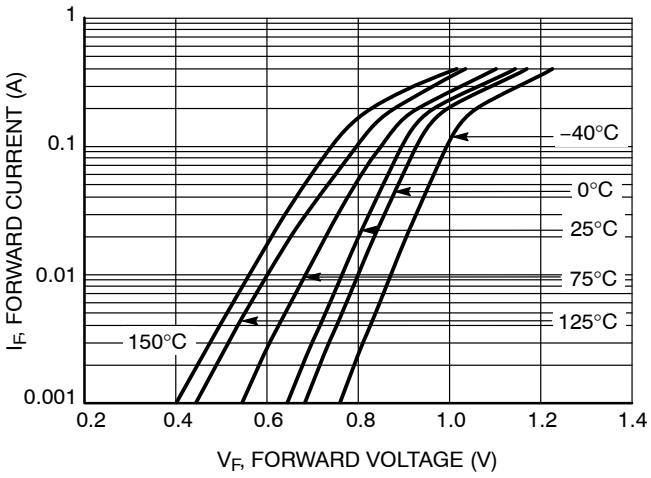


Figure 1. Forward Voltage

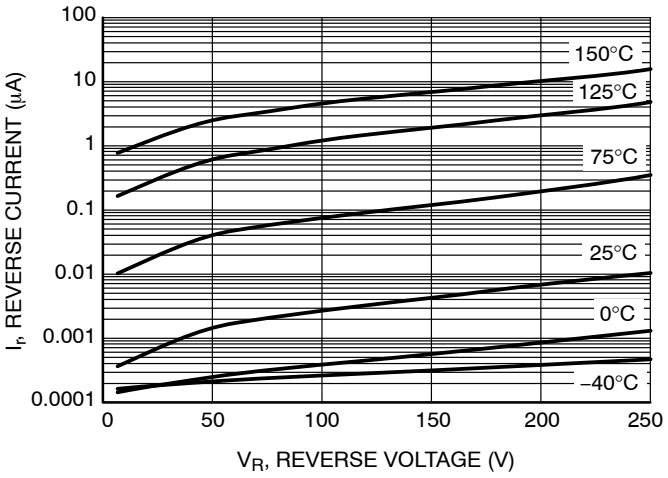


Figure 2. Reverse Current

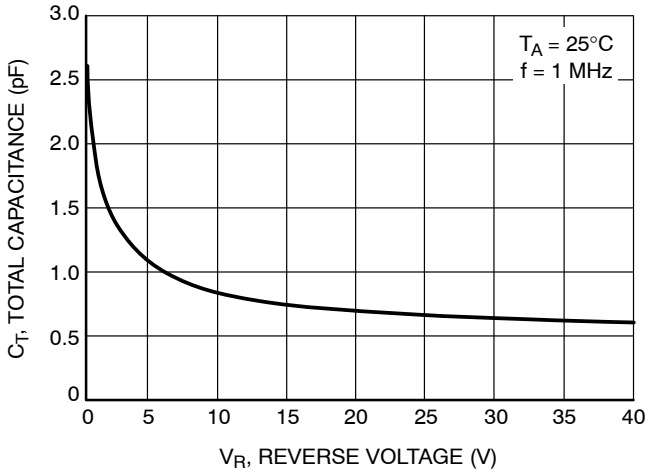
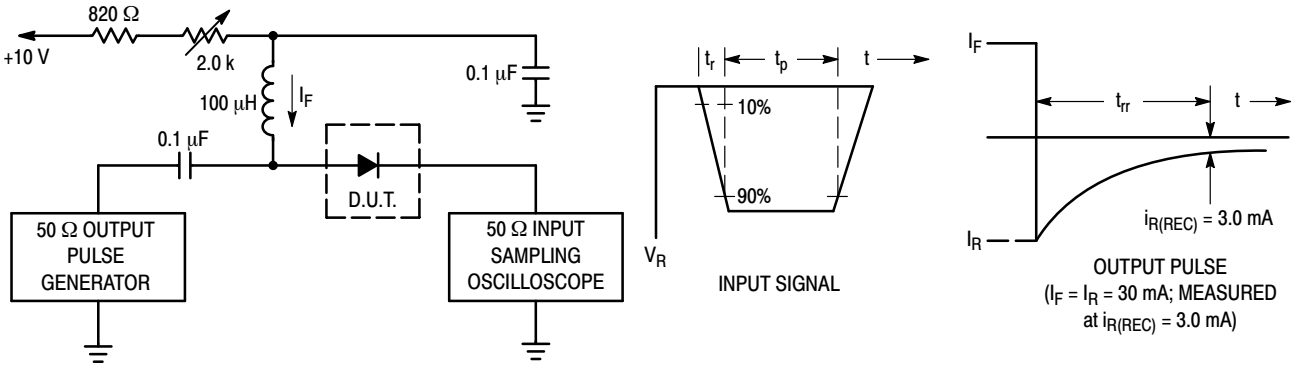


Figure 3. Total Capacitance

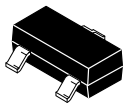


Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. t_p » t_{rr}

Figure 4. Recovery Time Equivalent Test Circuit

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

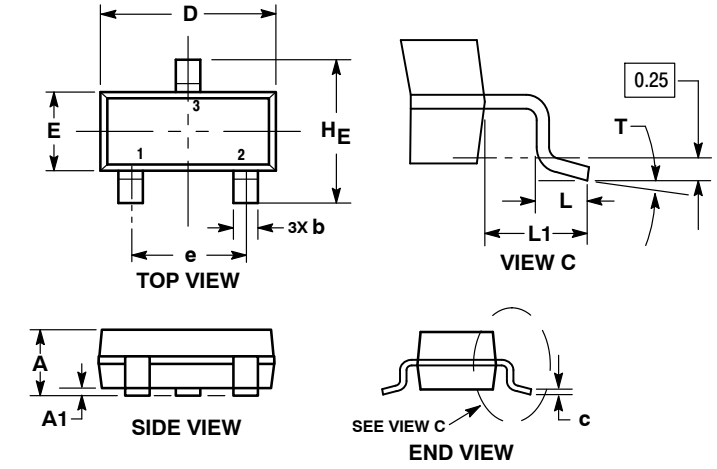
ON Semiconductor®



SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

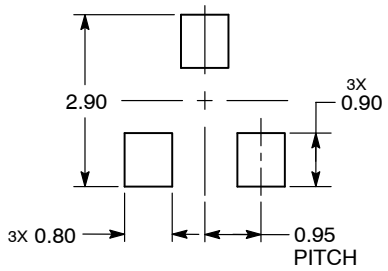
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

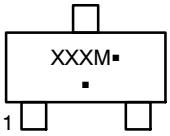
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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